

NPN SILICON HI FREQUENCY TRANSISTOR

DESCRIPTION:

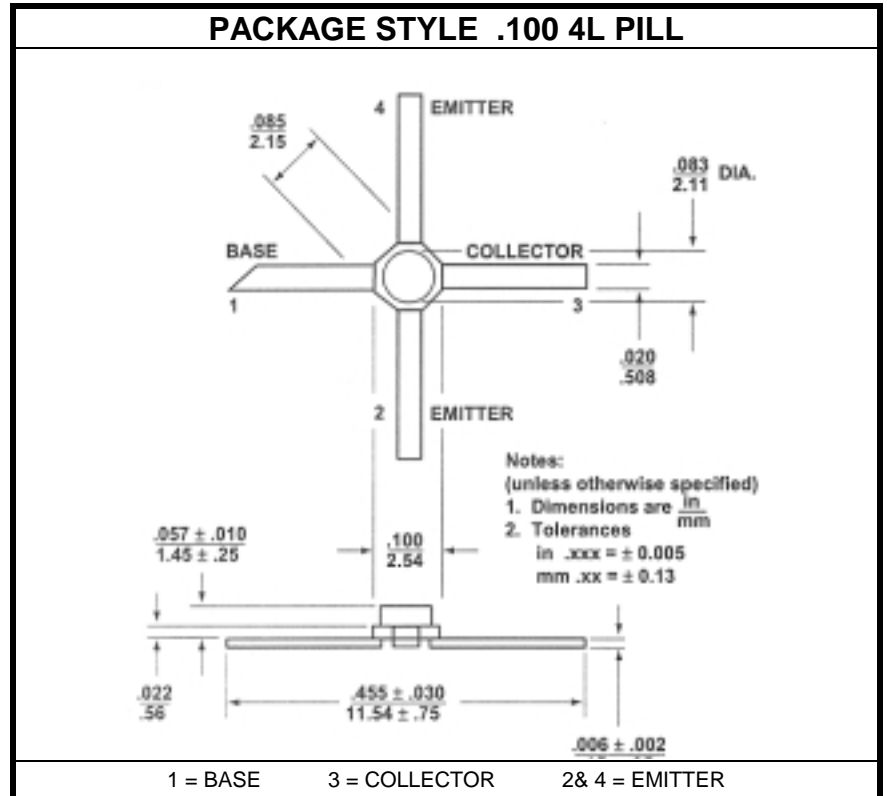
The **ASI NE21935** is Designed for general purpose and small signal amplifier and oscillator applications up to 6.0 GHz.

FEATURES INCLUDE:

- High frequency 8.0 GH
- Low noise, 1 dB at 0.5 GHz.

MAXIMUM RATINGS:

I_C	80 mA
V_{CB0}	20 V
V_{CEO}	10 V
V_{EBO}	1.5 V
P_{DISS}	580 mW @ T _A = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	80 °C/W


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
I_{CB0}	V _{CB} = 8.0 V				1.0	μA
I_{EBO}	V _{EB} = 1.0 V				1.0	μA
h_{FE}	V _{CE} = 8.0 V	I _C = 20 mA	30	100	300	---
C_{CB}	V _{CB} = 8.0 V	f = 1.0 MHz		0.4	1.0	pF
f_T	V _{CE} = 8.0 V	I _C = 20 mA		8.0		GHz
 S_{21E} 	V _{CE} = 8.0 V	I _C = 20 mA	f = 1.0 GHz	15.5		dB